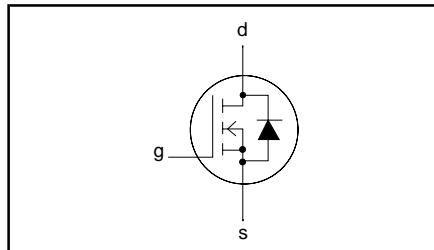


**N-channel TrenchMOS™ transistor****IRF530N****FEATURES**

- 'Trench' technology
- Low on-state resistance
- Fast switching
- Low thermal resistance

**SYMBOL****QUICK REFERENCE DATA**

$$V_{DSS} = 100 \text{ V}$$

$$I_D = 17 \text{ A}$$

$$R_{DS(ON)} \leq 110 \text{ m}\Omega$$

**GENERAL DESCRIPTION**

N-channel enhancement mode field-effect power transistor in a plastic envelope using 'trench' technology.

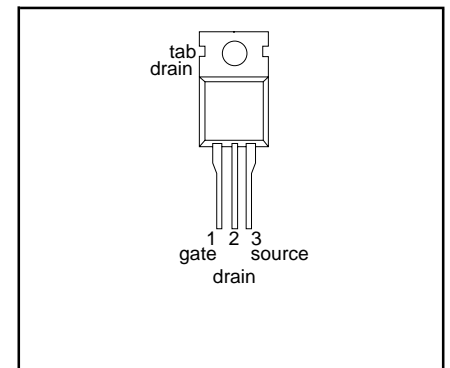
**Applications:-**

- d.c. to d.c. converters
- switched mode power supplies

The IRF530N is supplied in the SOT78 (TO220AB) conventional leaded package.

**PINNING**

PIN	DESCRIPTION
1	gate
2	drain
3	source
tab	drain

**SOT78 (TO220AB)****LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{DSS}$	Drain-source voltage	$T_j = 25^\circ\text{C}$ to $175^\circ\text{C}$	-	100	V
$V_{DGR}$	Drain-gate voltage	$T_j = 25^\circ\text{C}$ to $175^\circ\text{C}$ ; $R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	Gate-source voltage		-	$\pm 20$	V
$I_D$	Continuous drain current	$T_{mb} = 25^\circ\text{C}$ ; $V_{GS} = 10 \text{ V}$	-	17	A
		$T_{mb} = 100^\circ\text{C}$ ; $V_{GS} = 10 \text{ V}$	-	12	A
$I_{DM}$	Pulsed drain current	$T_{mb} = 25^\circ\text{C}$	-	68	A
$P_D$	Total power dissipation	$T_{mb} = 25^\circ\text{C}$	-	79	W
$T_j, T_{stg}$	Operating junction and storage temperature		- 55	175	$^\circ\text{C}$

**AVALANCHE ENERGY LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$E_{AS}$	Non-repetitive avalanche energy	Unclamped inductive load, $I_{AS} = 7.8 \text{ A}$ ; $t_p = 300 \mu\text{s}$ ; $T_j$ prior to avalanche = $25^\circ\text{C}$ ; $V_{DD} \leq 25 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; refer to fig:14	-	150	mJ
$I_{AS}$	Peak non-repetitive avalanche current		-	17	A

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## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	SOT78 package, in free air	-	-	1.9	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	60	-	K/W

## ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$ ; $I_D = 0.25\text{ mA}$ ; $T_j = -55^\circ\text{C}$	100 89	-	-	V V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ ; $I_D = 1\text{ mA}$ ; $T_j = 175^\circ\text{C}$ $T_j = -55^\circ\text{C}$	2 1 -	3 -	4 -	V V V
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 9\text{ A}$ ; $T_j = 175^\circ\text{C}$	- -	80 -	110 275	mΩ mΩ
$g_{fs}$	Forward transconductance	$V_{DS} = 25\text{ V}$ ; $I_D = 9\text{ A}$	6.4	11	-	S
$I_{GSS}$	Gate source leakage current	$V_{GS} = \pm 20\text{ V}$ ; $V_{DS} = 0\text{ V}$	-	10	100	nA
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 100\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $V_{DS} = 80\text{ V}$ ; $V_{GS} = 0\text{ V}$ ; $T_j = 175^\circ\text{C}$	- -	0.05 -	10 250	μA μA
$Q_{g(tot)}$	Total gate charge	$I_D = 9\text{ A}$ ; $V_{DD} = 80\text{ V}$ ; $V_{GS} = 10\text{ V}$	-	-	40	nC
$Q_{gs}$	Gate-source charge		-	-	5.6	nC
$Q_{gd}$	Gate-drain (Miller) charge		-	-	19	nC
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 50\text{ V}$ ; $R_D = 2.7\ \Omega$ ; $V_{GS} = 10\text{ V}$ ; $R_G = 5.6\ \Omega$	-	6	-	ns
$t_r$	Turn-on rise time	Resistive load	-	36	-	ns
$t_{d\ off}$	Turn-off delay time		-	18	-	ns
$t_f$	Turn-off fall time		-	12	-	ns
$L_d$	Internal drain inductance	Measured tab to centre of die	-	3.5	-	nH
$L_d$	Internal drain inductance	Measured from drain lead to centre of die (SOT78 package only)	-	4.5	-	nH
$L_s$	Internal source inductance	Measured from source lead to source bond pad	-	7.5	-	nH
$C_{iss}$	Input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 25\text{ V}$ ; $f = 1\text{ MHz}$	-	633	-	pF
$C_{oss}$	Output capacitance		-	103	-	pF
$C_{rss}$	Feedback capacitance		-	61	-	pF

## REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_S$	Continuous source current (body diode)		-	-	17	A
$I_{SM}$	Pulsed source current (body diode)		-	-	68	A
$V_{SD}$	Diode forward voltage	$I_F = 17\text{ A}$ ; $V_{GS} = 0\text{ V}$	-	0.92	1.2	V
$t_{rr}$	Reverse recovery time	$I_F = 17\text{ A}$ ; $-dI_F/dt = 100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$ ; $V_R = 25\text{ V}$	-	55	-	ns
$Q_{rr}$	Reverse recovery charge		-	135	-	nC

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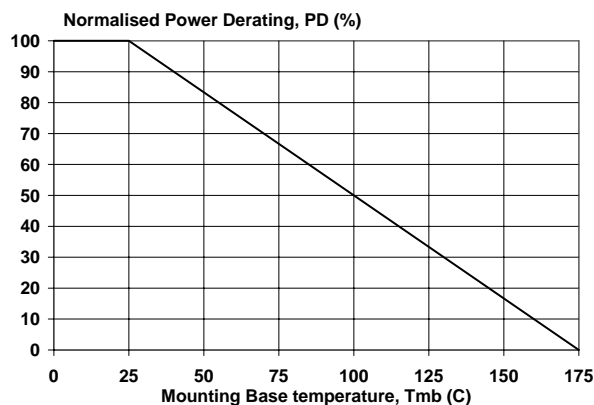


Fig. 1. Normalised power dissipation.  
 $PD\% = 100 \cdot P_D / P_{D, 25^\circ\text{C}} = f(T_{mb})$

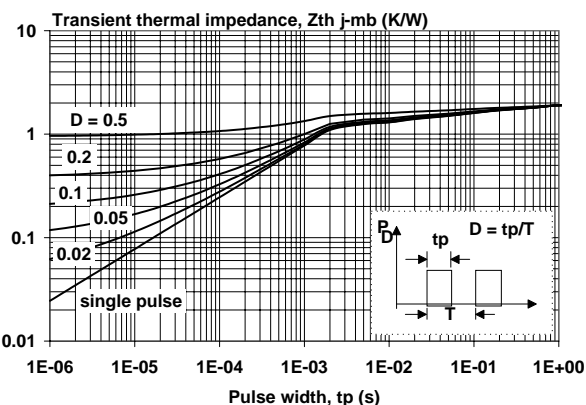


Fig. 4. Transient thermal impedance.  
 $Z_{th j-mb} = f(t)$ ; parameter  $D = t_p/T$

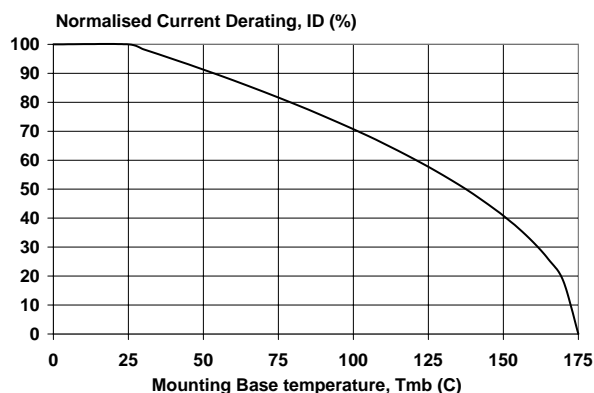


Fig. 2. Normalised continuous drain current.  
 $ID\% = 100 \cdot I_D / I_{D, 25^\circ\text{C}} = f(T_{mb})$ ; conditions:  $V_{GS} \geq 10\text{ V}$

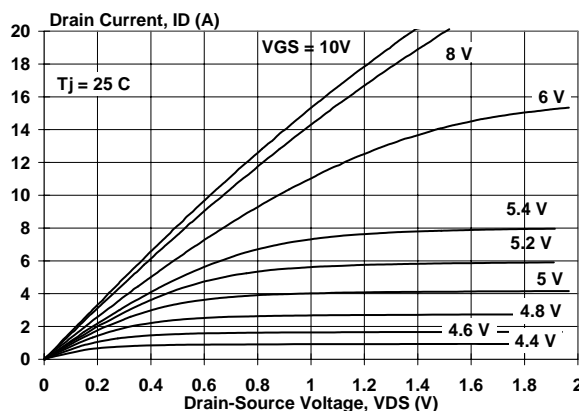


Fig. 5. Typical output characteristics,  $T_j = 25^\circ\text{C}$ .  
 $I_D = f(V_{DS})$

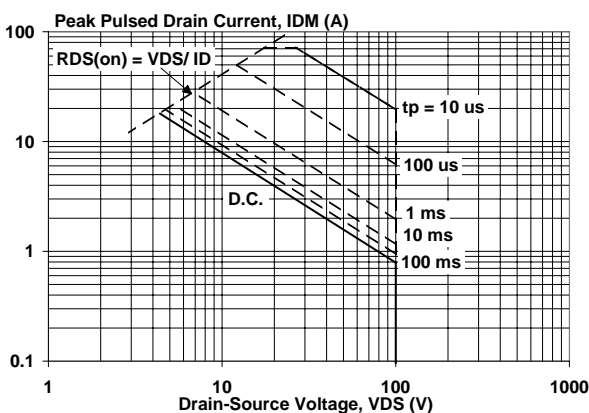


Fig. 3. Safe operating area.  $T_{mb} = 25^\circ\text{C}$   
 $I_D$  &  $I_{DM} = f(V_{DS})$ ;  $I_{DM}$  single pulse; parameter  $t_p$

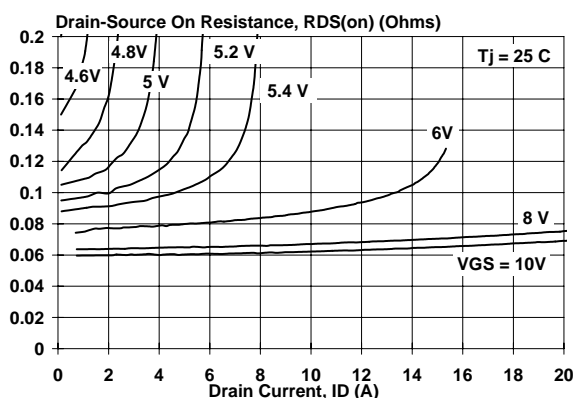
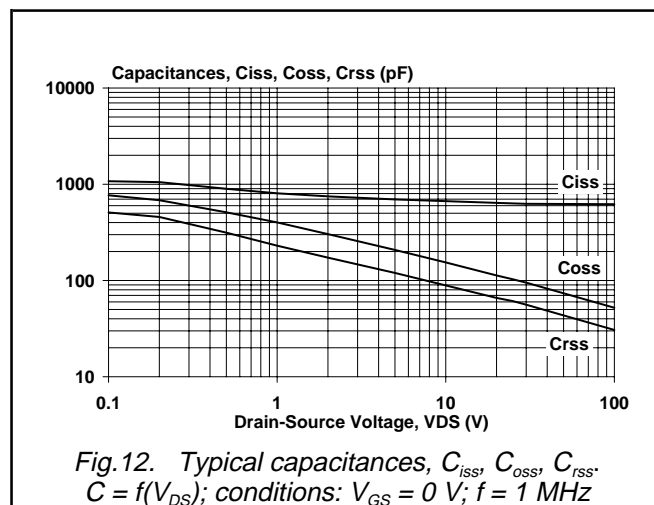
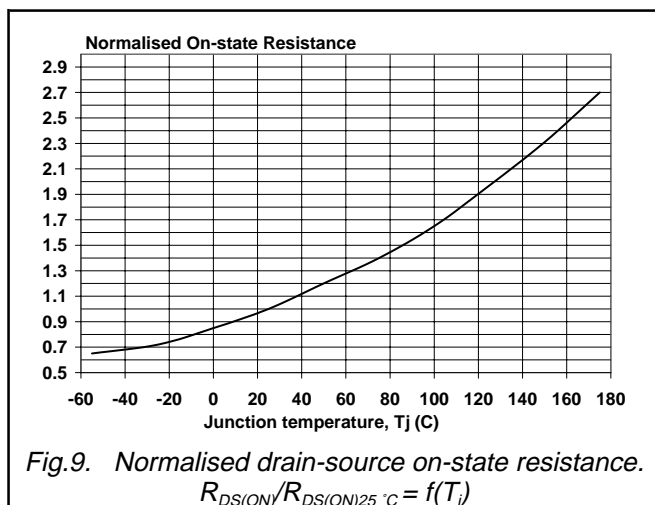
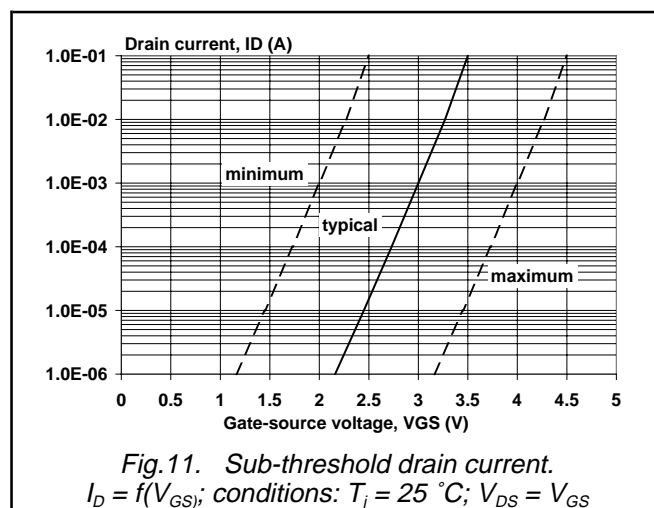
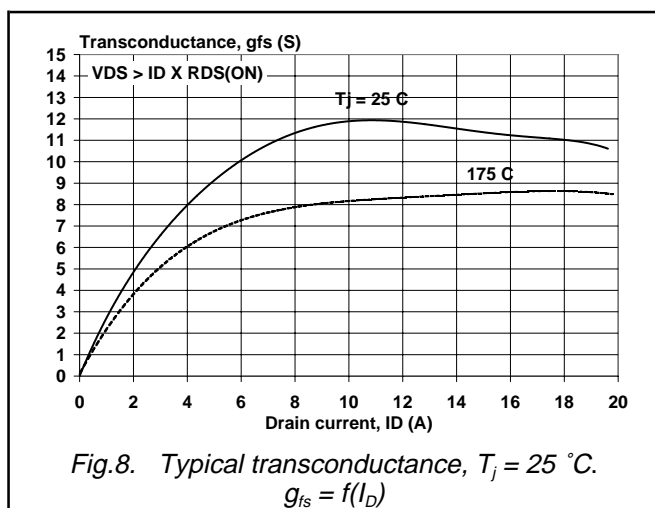
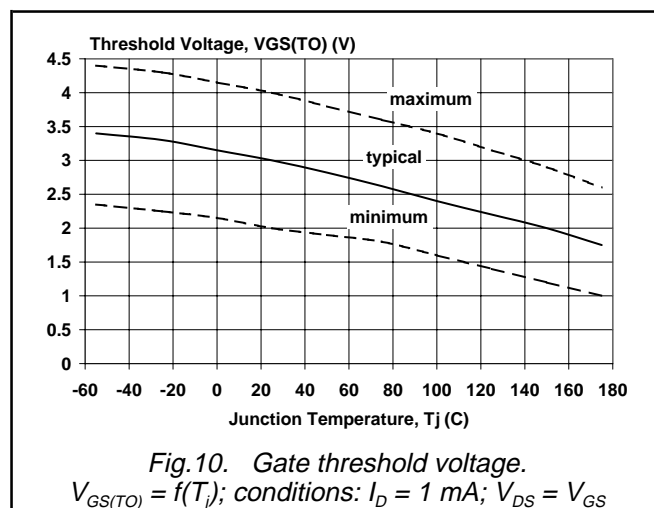
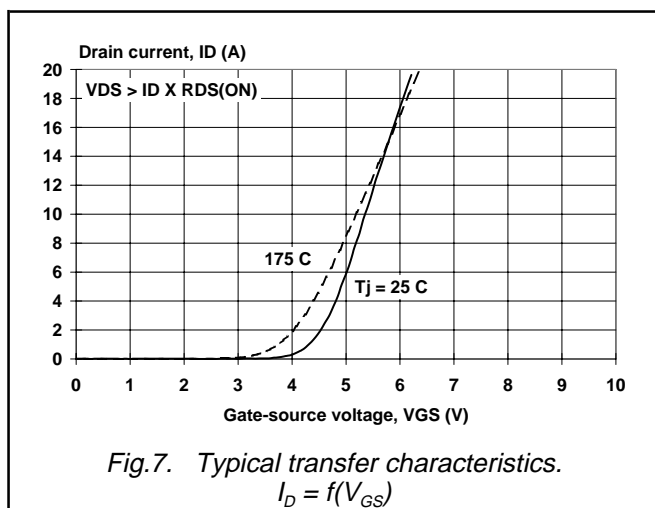


Fig. 6. Typical on-state resistance,  $T_j = 25^\circ\text{C}$ .  
 $R_{DS(ON)} = f(I_D)$

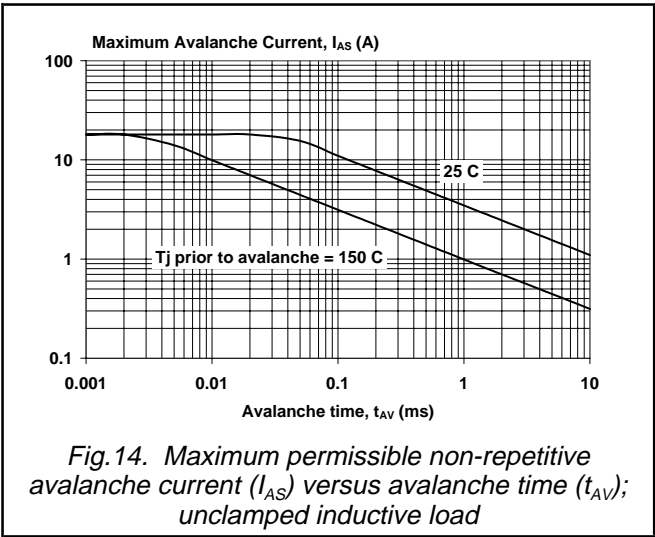
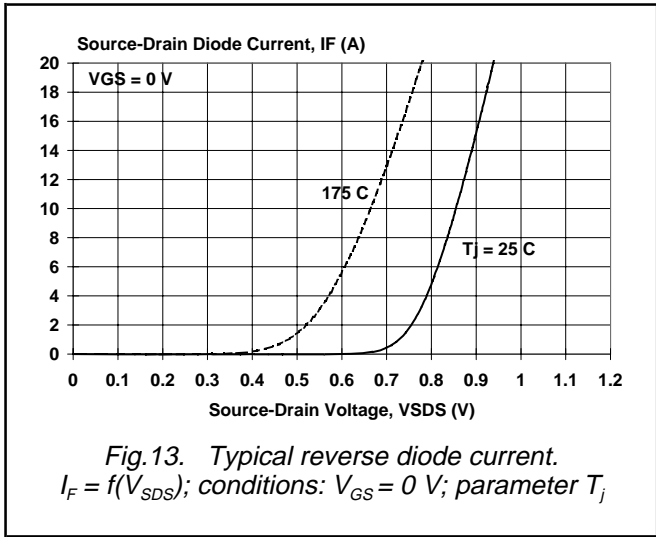
N-channel TrenchMOS<sup>TM</sup> transistor

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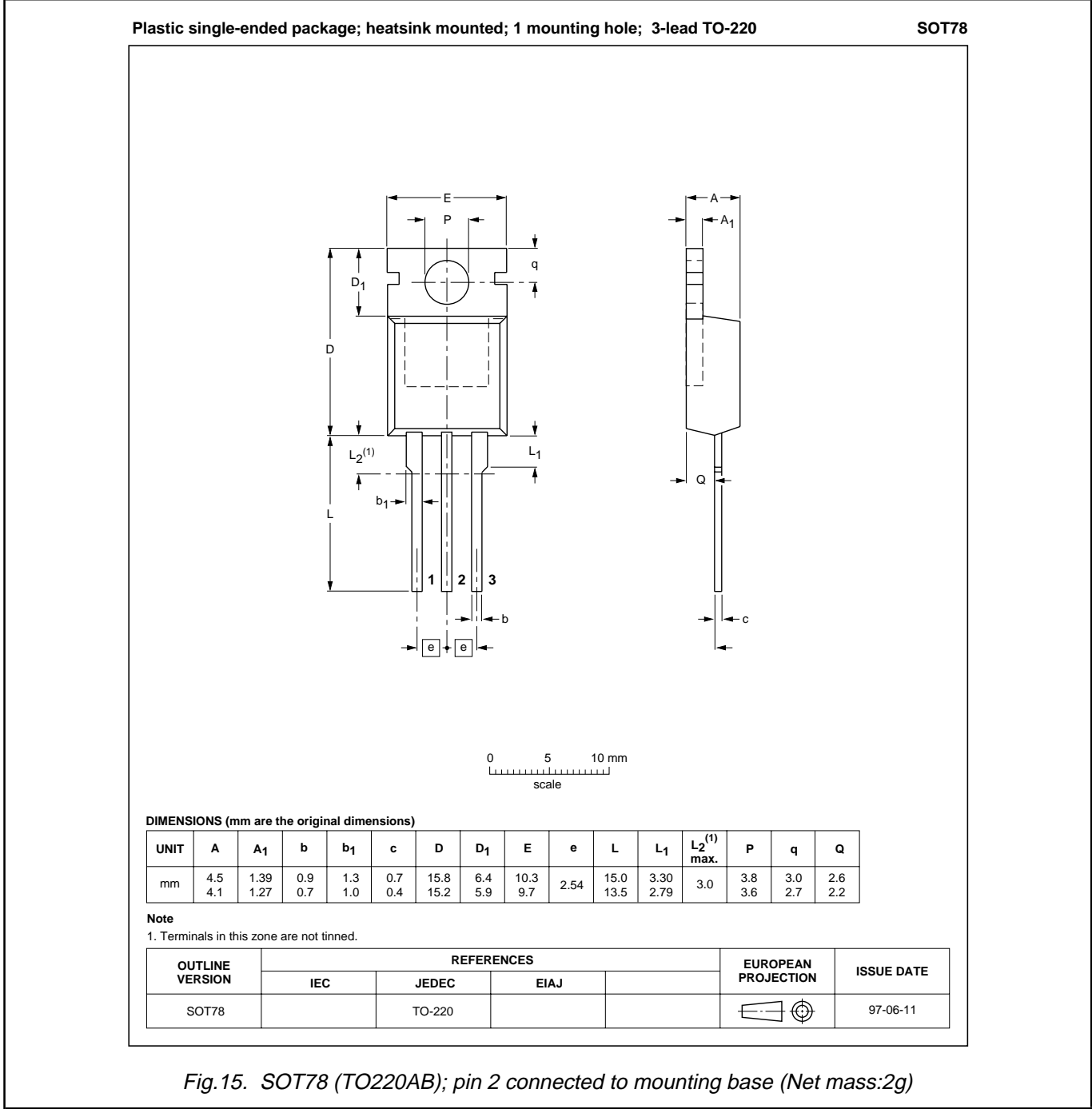
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MECHANICAL DATA



Notes

1. This product is supplied in anti-static packaging. The gate-source input must be protected against static discharge during transport or handling.
2. Refer to mounting instructions for SOT78 (TO220AB) package.
3. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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